

ABSTRACT OF THE DISCLOSURE

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The present invention relates to a semiconductor memory device having a SRAM in which a memory cell

5 comprises a pair of transmission transistors and a flip-flop circuit containing a pair of driver transistors and a pair of load transistors, wherein: a first conductive film interconnection formed from a first conductive film which is set on a semiconductor substrate, constitutes

10 respective gate electrodes of said driver transistors, load transistors and transmission transistors; an inlaid interconnection set in a first insulating film lying on said semiconductor substrate, constitutes one of a pair of local interconnections cross-coupling a pair of

15 input/output terminals in said flip-flop circuit; and a second conductive film interconnection formed from a second conductive film which is set on a second insulating film lying on said first insulating film, constitutes the other one of said pair of local

20 interconnections.